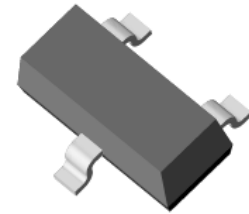


High Voltage Switching Diode

General Description

Dual general-purpose switching diodes, fabricated in planar technology, and packaged in small SOT-23F surface mounted device (SMD) packages.



SOT-23F



Features and Benefits

- Silicon epitaxial planar diode
- High switching speed
- Low forward drop voltage and low leakage current
- “Green” device and RoHS compliant device
- Available in full lead (Pb)-free device

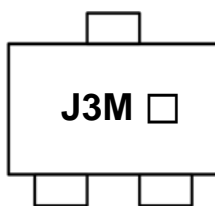
Applications

- Ultra high speed switching application

Ordering Information

Part Number	Marking Code	Package	Packaging
SDS20WMF	J3M □	SOT-23F	Tape & Reel

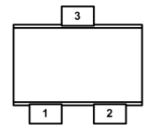
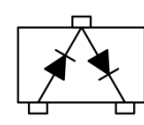
Marking Information



J3M = Specific Device Code

□ = Year & Week Code Marking

Pinning Information

Pin	Description	Simplified Outline	Graphic Symbol
1	Anode (Diode 1)		
2	Cathode (Diode 2)		
3	Cathode (Diode 1), Anode (Diode 2)		

Absolute Maximum Ratings (T_{amb}=25°C, Unless otherwise specified)

Characteristic	Symbol	Ratings	Unit
Maximum repetitive peak reverse voltage	V _{RM}	200	V
Continuous reverse voltage	V _R	150	V
Maximum average forward rectified current	I _O	200	mA
Maximum repetitive peak forward current	I _{FM}	400	mA
Non-repetitive peak forward surge current(t=10ms)	I _{FSM}	1.7	A
Power dissipation ¹⁾	P _D	250	mW

¹⁾ Device mounted on FR-4 board with recommended pad layout.

Thermal Characteristics (T_{amb}=25°C, Unless otherwise specified)

Characteristic	Symbol	Ratings	Unit
Thermal resistance, junction to ambient ¹⁾	R _{th(j-a)}	500	°C/W
Operating junction temperature	T _j	150	°C
Storage temperature range	T _{stg}	-55 ~ 150	°C

¹⁾ Device mounted on FR-4 board with recommended pad layout.

Electrical Characteristics (T_{amb}=25°C, Unless otherwise specified)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Reverse breakdown voltage	V _{BR}	I _F =100uA	200	-	-	V
Forward drop voltage ²⁾	V _F	I _F =100mA	-	-	1.0	V
		I _F =200mA	-	-	1.25	V
Reverse leakage current ³⁾	I _R	V _R =150V	-	-	100	nA
		V _R =150V, Ta=150°C	-	-	100	uA
Total capacitance	C _T	V _R =0V, f=1MHz	-	-	5	pF
Reverse recovery time	t _{rr}	I _F =I _R =30mA, I _{rr} =3mA, R _L =100Ω	-	-	50	ns

²⁾ Pulse test: t_p≤380μs, Duty cycle≤2%

³⁾ Pulse test: t_p≤5ms, Duty cycle≤2%

Rating and Characteristic Curves

Fig. 1) Typical Forward Characteristics

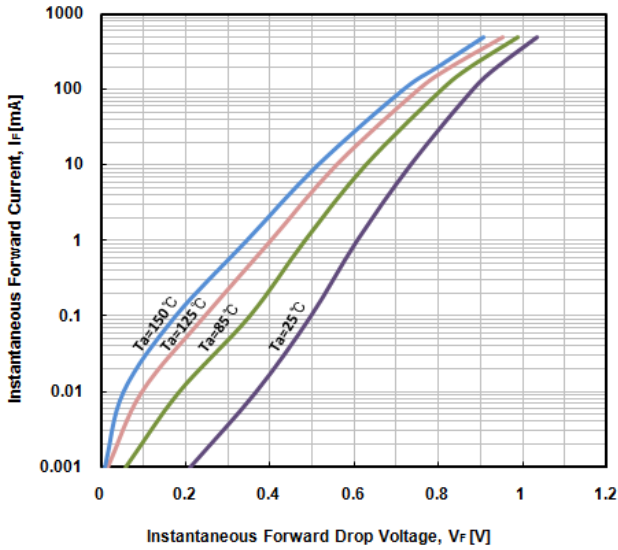


Fig. 2) Typical Reverse Characteristics

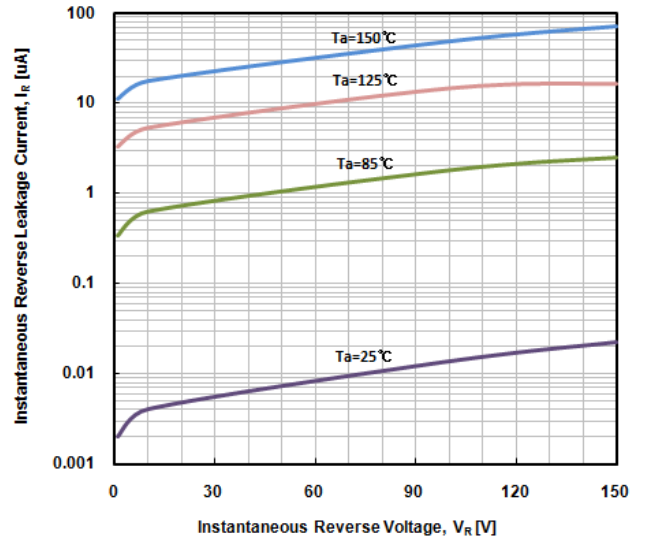


Fig. 3) Typical Total Capacitance Characteristics

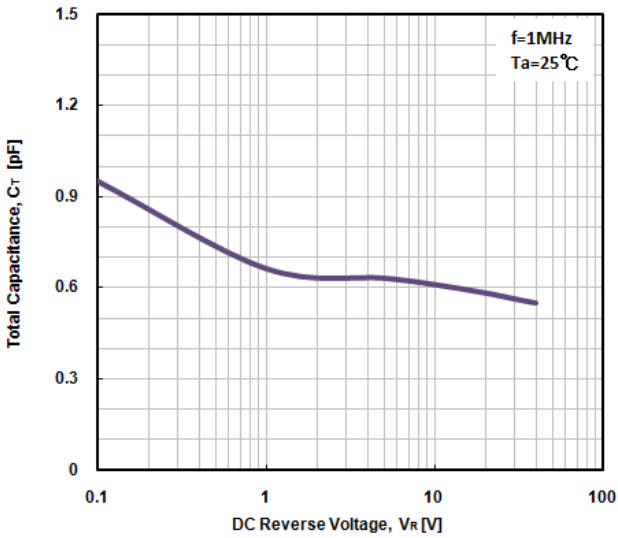


Fig. 4) Power Dissipation vs. Ambient Temperature

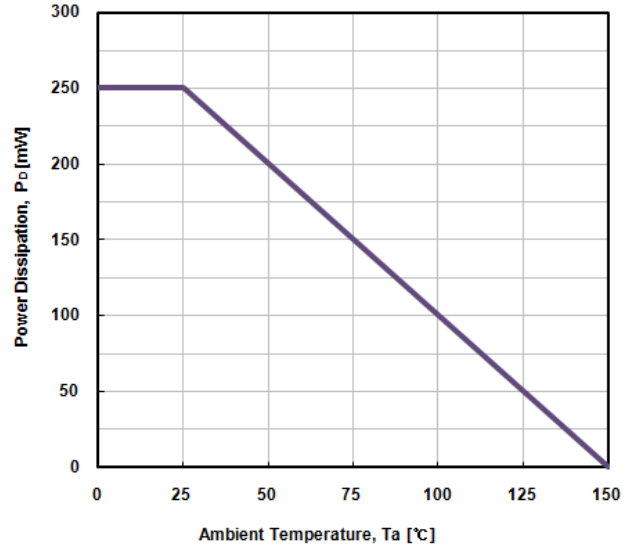
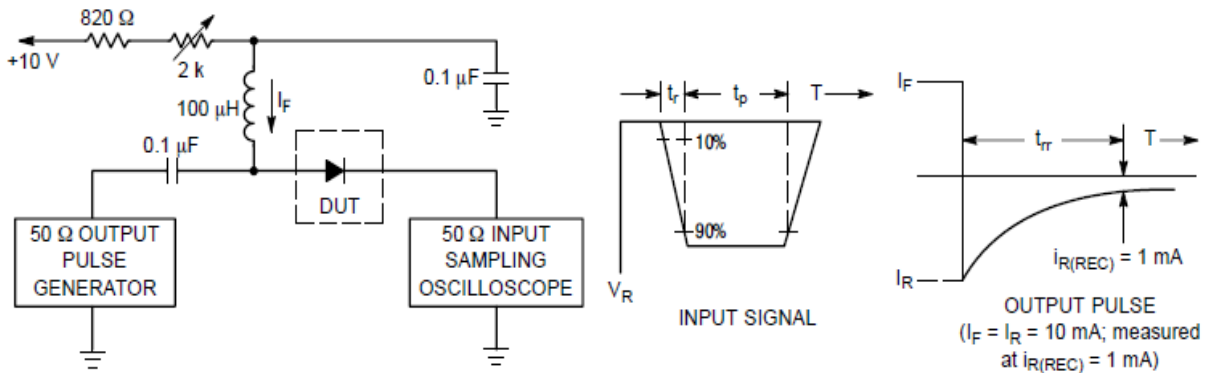
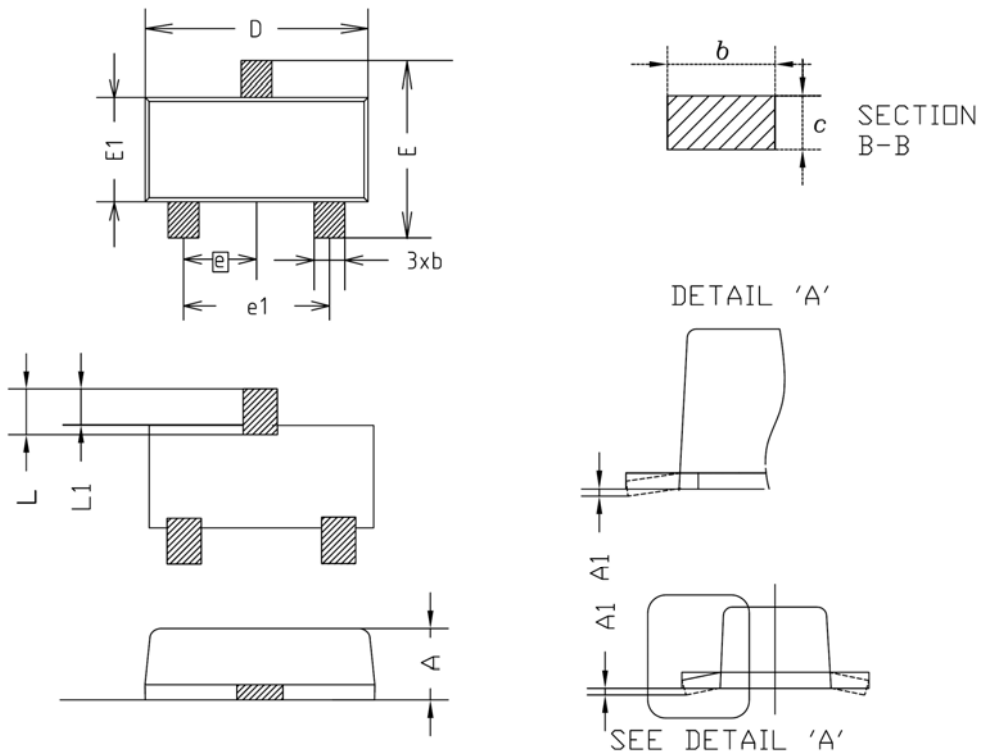


Fig. 5) Reverse recovery time equivalent test circuit

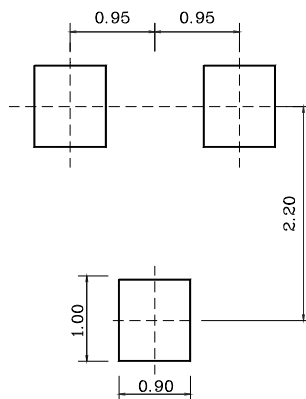


Package Outline Dimensions



SYMBOL	MILLIMETER(mm)			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	0.80	0.90	1.00	
A1	0.00	-	0.10	
b	0.35	0.40	0.45	
c	0.10	0.15	0.20	
D	2.80	2.90	3.00	
E	2.30	2.40	2.50	
E1	1.50	1.60	1.70	
e	0.95BSC			
e1	1.80	1.90	2.00	
L	0.48	0.58	0.68	
L1	0.30	-	0.50	

※ Recommend PCB solder land (Unit : mm)



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